



U.S. PTO
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0560 U.S. PTO

UTILITY PATENT APPLICATION TRANSMITTAL

(Only for new nonprovisional applications under 37 CFR 1.53(b))

Attorney Docket No.

35.G2254

First Named Inventor or Application Identifier

HIDEO KATO, ET AL.

Express Mail Label No.

APPLICATION ELEMENTS

See MPEP chapter 600 concerning utility patent application contents.

ADDRESS TO:

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1. ☒ Fee Transmittal Form
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- a. ☐ Newly executed (original or copy)
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- c. ☐ Copy from a prior application (37 CFR 1.63(d))
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- i. ☐ **DELETION OF INVENTOR(S)**
Signed Statement attached deleting inventor(s) named in
the prior application, see 37 CFR 1.63(d)(2) and 1.33(b).
5. ☐ Incorporation By Reference (useable if Box 4c is checked)
The entire disclosure of the prior application, from which a copy of the oath or
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8. ☐ Assignment Papers (cover sheet & documents)
9. ☐ 37 CFR 3.73(b) Statement ☐ Power of Attorney
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11. ☐ Information Disclosure Statement (IDS)/PTO-1449 ☐ Copies of IDS
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12. ☐ Preliminary Amendment
13. ☒ Return Receipt Postcard (MPEP 503)
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14. ☐ Small Entity Statement(s) ☐ Statement filed in prior application
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CLAIMS	(1) FOR	(2) NUMBER FILED	(3) NUMBER EXTRA	(4) RATE	(5) CALCULATIONS
	TOTAL CLAIMS (37 CFR 1.16(c))	42-20 -	21	X \$ 22.00 -	\$ 462.00
	INDEPENDENT CLAIMS (37 cfr 1.16(b))	10-3 -	7	X \$ 82.00 -	\$ 574.00
	MULTIPLE DEPENDENT CLAIMS (if applicable) (37 CFR 1.16(d))			\$270.00 -	\$ 270.00
				BASIC FEE (37 CFR 1.16(a))	\$ 790.00
			Total of above Calculations -		\$2096.00
	Reduction by 50% for filing by small entity (Note 37 CFR 1.9, 1.27, 1.28).				
	TOTAL -				\$2096.00

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- a. ☐ A Small entity statement is enclosed
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20. ☒ A check in the amount of \$ 2096.00 to cover the filing fee is enclosed.

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- a. ☒ Fees required under 37 CFR 1.16.
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SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED	
NAME	Steven E. Warner, Reg. No. 33,326
SIGNATURE	
DATE	September 24, 1998

TITLE OF THE INVENTION

ILLUMINATOR, EXPOSURE APPARATUS, AND METHOD FOR FABRICATING
DEVICE USING THE SAME

5

BACKGROUND OF THE INVENTION

Field of the Invention

10 The present invention relates to an illumination
apparatus (illuminator), an exposure apparatus, and a method
for fabricating devices using the same. In particular, the
present invention is suitable for fabricating devices, for
example, semiconductor devices such as ICs and LSIs, liquid
crystal devices, image devices such as CCDs, and magnetic
15 heads. The reason for this is that a titanium oxide (TiO_2)
film, provided on a portion of an optical unit included in
an exposure apparatus such as a projection exposure
apparatus (projection aligner) or on a portion of a
supporting unit for supporting the optical unit, effectively
20 prevents dust, hazardous substances in the air, and the like
from adhering to and contaminating the surface of each unit
even when far ultraviolet light is used as exposure light
for long periods of time.

Description of the Related Art

25

With respect to photolithography in fabricating

semiconductor devices, there has been a shift in exposure light to be used from the visible region to the ultraviolet region for the purpose of fabricating high-integration devices. In recent applications of photolithography, a
5 laser such as an excimer laser is being used as a light source instead of a mercury lamp. Also, in recent applications of lithography, there has been a shift in the environment in which projection and exposure are performed from in the air to in a non-oxygen atmosphere, such as
10 nitrogen, reduced-pressure, or vacuum atmosphere. Besides, chemically amplified resists using acid catalysts are becoming popular. Also, there have been considerable changes in specifications required for optical materials (i. e., optical units) such as optical elements, for example,
15 lenses and mirrors, included in optical systems used for reduction-type projection aligners such as steppers, fabrication apparatuses, and processes.

Chemical contamination in a clean room in which photolithography is performed may be caused by breakdown
20 substances by photoreaction of a resist, scattered substances during coating, development, baking, cleaning, and other processes, and vaporized substances from adhesives and wall materials. These substances float in the air with a considerable density. Because of the substances described
25 above, surfaces of optical elements such as lenses, mirrors,

and prisms are considerably contaminated after they are exposed for a long time by KrF or ArF excimer laser light, or deep ultraviolet light for exposure. It is pointed out that the substances adhered to the surfaces significantly decrease optical properties such as transmittance and reflectance. Generally, these substances vary in shape and composition, and although there is a certain tendency depending on the environment, reasons for adhesion are not clear. It may be inferred from the above that decomposition, recombination, multiple reactions, deposition, crystallization, and the like, act complexly instead of a simple photochemical reaction.

Contamination of optical units is a big problem, particularly with steppers, which are used for fabrication of semiconductor devices, and also is a big problem with optical systems for other usages such as lens systems for still cameras, lens systems for video cameras, lens systems for telescopes, and lenses, mirrors, prisms, and diffraction gratings for microscopes and measuring instruments.

SUMMARY OF THE INVENTION

It is an object of the present invention to provide an illuminator, an exposure apparatus, and a method for fabricating devices using the same, in which optical properties do not decrease.

In accordance with an illuminator of the present invention,

(1-1) in one aspect, an illuminator for illuminating a surface to be illuminated with a luminous flux from a light source through an illumination system includes a titanium oxide film provided on the surface of at least one unit which constitutes the illumination system;

(1-2) in another aspect, an illuminator for illuminating a surface to be illuminated with a luminous flux from a light source through an illumination system includes a titanium oxide film provided on the surface of at least one region of at least one optical unit among a plurality of optical units placed in an optical path from the light source to the surface to be illuminated; and

(1-3) in still another aspect, an illuminator for illuminating a surface to be illuminated with a luminous flux from a light source through an illumination system includes a titanium oxide film provided on the surface of at least one region of at least one supporting unit among a plurality of supporting units for supporting at least one optical unit among a plurality of optical units placed in an optical path from the light source to the surface to be illuminated.

Preferably, in an illuminator of the present invention according to (1-1), (1-2), or (1-3),

the luminous flux is ultraviolet light, and the titanium oxide film prevents contaminants, for example, dust and hazardous substances in the air, from adhering to and contaminating the unit provided with the titanium oxide film or its adjacent unit by a photoconductive function such as photoconduction and a photocatalytic reaction caused by the absorption of the ultraviolet light;

the unit or the optical unit includes at least one of a diaphragm, a shutter, and a lens barrel;

the unit or the optical unit includes at least one of a lens, a mirror, a prism, a filter, a diffuser, a diffraction optical element, and an optical integrator;

the unit or the optical unit includes a diffraction optical lens using a diffraction optical element, or a mirror;

the titanium oxide film is provided on the surface of a portion of a region of the optical unit in which light passes through; and

the titanium oxide film has a thickness ranging from 10 nm to 100 nm.

In accordance with an exposure apparatus of the present invention,

(2-1) in one aspect, an exposure apparatus for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and exposing a

substrate with the pattern includes a titanium oxide film provided on the surface of at least one unit among a plurality of units which constitute the exposure apparatus;

(2-2) in another aspect, an exposure apparatus for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and exposing a substrate with the pattern includes a titanium oxide film provided on the surface of at least one region of at least one optical unit among a plurality of optical units placed in an optical path from the light source to the substrate; and

(2-3) in still another aspect, an exposure apparatus for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and exposing a substrate with the pattern includes a titanium oxide film provided on the surface of at least one region of at least one supporting unit among a plurality of supporting units for supporting at least one optical unit among a plurality of optical units placed in an optical path from the light source to the substrate.

Preferably, in an exposure apparatus of the present invention according to (2-1), (2-2), or (2-3),

the luminous flux is ultraviolet light, and the titanium oxide film prevents contaminants, for example, dust and hazardous substances in the air, from adhering to and

contaminating the unit provided with the titanium oxide film or its adjacent unit by a photoconductive function such as photoconduction and a photocatalytic reaction caused by the absorption of the ultraviolet light;

5 the unit includes at least one of a diaphragm, a shutter, and a lens barrel;

 the unit or the optical unit includes at least one of a lens, a mirror, a prism, a filter, a diffuser, a diffraction optical element, and an optical integrator;

10 the unit or the optical unit includes a diffraction optical lens using a diffraction optical element, or a mirror;

15 the titanium oxide film is provided on the surface of a portion of a region of the optical unit in which light passes through;

 exposure is performed while the pattern on the mask and the substrate are synchronously scanned; and

 the titanium oxide film has a thickness ranging from 10 nm to 100 nm.

20 In accordance with a method for fabricating devices of the present invention,

 (3-1) a method includes the steps of exposing a wafer with a device pattern formed on a reticle using an exposure apparatus according to any one of (2-1) through (2-3), and
25 developing the wafer.

In accordance with a projection aligner of the present invention,

(4-1) in one aspect, a projection aligner for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and projecting the pattern onto a wafer by a projection optical system includes a titanium oxide film provided on the surface of at least one unit which constitutes the projection aligner;

(4-2) in another aspect, a projection aligner for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and projecting the pattern onto a wafer by a projection optical system includes a titanium oxide film provided on the surface of at least one region of at least one optical unit among a plurality of optical units placed in an optical path from the light source to the wafer; and

(4-3) in still another aspect, a projection aligner for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and projecting the pattern onto a wafer by a projection optical system includes a titanium oxide film provided on the surface of at least one region of at least one supporting unit among a plurality of supporting units for supporting one or a plurality of optical units placed in an optical path from the light source to the wafer.

Preferably, in a projection aligner of the present invention according to (4-1), (4-2), or (4-3), the luminous flux is ultraviolet light, and the titanium oxide film prevents contaminants, for example, dust and hazardous substances in the air, from adhering to and contaminating a surface of the unit provided with the titanium oxide film through a photoconductive function such as photoconduction and a photocatalytic reaction caused by the absorption of the ultraviolet light;

the unit includes at least one of a diaphragm, a shutter, and a lens barrel;

the unit includes at least one of a lens, a mirror, a prism, a filter, a diffuser, a diffraction optical element, and an optical integrator;

the unit includes a diffraction optical lens using a diffraction optical element, or a mirror;

the titanium oxide film is provided in a portion of a region through which light passes on the surface of the optical unit;

projection and exposure are performed while the pattern on the mask and the wafer are synchronously scanned at a velocity ratio in response to imaging magnification of the projection optical system; and

the titanium oxide film has a thickness ranging from 10 nm to 100 nm.

In accordance with a method for fabricating devices of the present invention,

(5-1) a method includes the steps of projecting a device pattern formed on a reticle onto a wafer after the reticle is aligned with the wafer using a projection aligner according to any one of (4-1) through (4-3), and developing the wafer.

Further objects, features and advantages of the present invention will become apparent from the following description of the preferred embodiments with reference to the attached drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic diagram of the key portion of a system for fabricating semiconductor devices using an exposure apparatus in accordance with the present invention;

FIG. 2 is a schematic diagram of a first example in which a TiO_2 film is provided on the surface of a unit constituting an exposure apparatus in accordance with the present invention;

FIG. 3 is a schematic diagram of a second example in which a TiO_2 film is provided on the surface of a unit constituting an exposure apparatus in accordance with the present invention;

FIG. 4 is a schematic diagram of a fourth example in

which a TiO_2 film is provided on the surface of a unit constituting an exposure apparatus in accordance with the present invention;

FIG. 5 is a schematic diagram of a seventh example in which a TiO_2 film is provided on the surface of a unit constituting an exposure apparatus in accordance with the present invention;

FIG. 6 is a schematic diagram of an eighth example in which a TiO_2 film is provided on the surface of a binary optics lens constituting an exposure apparatus in accordance with the present invention;

FIG. 7 is a schematic diagram of a ninth example in which a TiO_2 film is provided on the surface of a binary optics lens constituting an exposure apparatus in accordance with the present invention;

FIG. 8 is a flow chart which shows a method for fabricating devices in accordance with the present invention; and

FIG. 9 is a detailed flow chart of a wafer process.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

FIG. 1 is a schematic diagram of the key portion of a projection aligner and a system for fabricating devices using the same, as a first embodiment of the present invention.

In accordance with this embodiment, a circuit pattern formed on a reticle, a photomask, or the like (generically called a "mask") is printed onto a wafer (i.e., photosensitive substrate) to fabricate a semiconductor device. The system includes a projection aligner, a container for masks, an inspection unit for original masks, and a controller, which are all placed in a clean room.

In FIG. 1, numeral 1 represents an excimer laser containing KrF, ArF, or the like, as a light source, for radiating ultraviolet light or far ultraviolet light. A high-pressure mercury-vapor lamp (i-line light) may be used instead of an excimer laser. Numeral 2 represents an illumination system as a unit for illuminating a reticle 3 set at an exposure position E.P. from above with a given numerical aperture (NA). Numeral 4 represents a projection optical system (projection lens) for reduction projecting and printing a circuit pattern formed on the reticle 3 onto a wafer 5 such as a silicon substrate. Numeral 6 represents an alignment system for aligning the reticle 3 with the wafer 5 prior to an exposure operation. The alignment system 6 is provided with a microscope system for observing reticles. Numeral 7 represents a wafer stage. The units 1 through 6 described above constitute the projection aligner.

Numeral 8 represents a container for containing a plurality of reticles as masks. Numeral 9 represents an

inspection unit for detecting foreign particles on reticles. The inspection unit 9 inspects foreign particles on a reticle before the selected reticle from the container 8 is set at the exposure position E.P.

5 A controller 10 controls the sequence of the entire system, including commands for operating the container 8 and the inspection unit 9, and sequences such as alignment, exposure, and step-feed of wafers, which are the basic operations of a projection aligner.

10 In accordance with this embodiment, a step-and-repeat projection aligner or a step-and-scan projection aligner is used. With respect to the step-and-scan projection aligner, projection and exposure are performed while the reticle 3 and the wafer 5 are scanned synchronously at a velocity
15 ratio in response to imaging magnification of the projection optical system 4.

Also, in accordance with this embodiment, a proximity aligner, in which exposure is performed without a projection lens, may be used in the same manner, instead of a
20 projection aligner.

In accordance with this embodiment, the illumination system 2, the projection optical system 4, the inspection unit 9 and the alignment system 6 employ various optical units (optical elements) such as lenses, mirrors, prisms,
25 diffraction optical elements (binary optics elements, i.e.,

BO elements).

A titanium oxide (TiO_2) film is provided on the surface of one or all of these optical units and at least on a portion of the surface of at least one supporting unit (lens barrel) for supporting one or all of the optical units. This effectively prevents dust, hazardous substances in the air, and the like from adhering to and contaminating the surface of each unit even when the fabrication of semiconductor devices is performed for a long period of time.

The TiO_2 film used in this embodiment is effective as a photo semiconductor by absorbing ultraviolet light, in particular, far ultraviolet light. The typical functions as a photo semiconductor include, the antistat effect by photoconduction, the decomposition reaction as a photocatalyst, the reduction in the angle of contact toward water, and the antibacterial reaction. Since TiO_2 has a high refractive index and absorbency in the ultraviolet region, the TiO_2 film must be thin when provided on the surface of an optical unit.

When TiO_2 is evaporated onto the surface of an optical unit, the thickness of the TiO_2 film will be approximately 100 nm at the most. On condition that the TiO_2 film is irradiated with a powerful beam such as a laser beam, it functions as a photo semiconductor sufficiently even at a thickness of approximately 10 nm. Therefore, in accordance

with the present invention, the thickness of the TiO_2 film is set at 10 nm to 100 nm. When there is a decrease in optical properties such as transmittance, the TiO_2 film is provided partially only on the periphery of optical elements (units).

5 In accordance with the present embodiment, in order to deposit a TiO_2 film onto the surface of each unit, a vapor deposition process may be used, or the film may be formed by hydrolysis caused by heating after the surface is preliminarily coated with alkyltitanate.

10 Next, typical examples in which TiO_2 is applied on the surfaces of optical units or supporting units constituting the individual apparatuses will be described one by one.

Example 1

15 A TiO_2 film at a thickness of 10 nm was evaporated by a resistance heating evaporation system onto the surface of a portion of lenses constituting a projection optical system composed of quartz for a KrF stepper (a step-and-repeat or step-and-scan reduction-type projection aligner). The portion of lenses corresponded to one lens out of
20 approximately 20 lenses constituting the projection optical system.

In a conventional apparatus, which does not use a TiO_2 film, adhesion was observed on the surface of each lens constituting a projection optical system after being used
25 for approximately 6 months. In accordance with the present

embodiment, only one of the lenses constituting the projection optical system was applied with TiO_2 treatment.

When the surface of the lens was inspected after a steady operation for 6 months, significantly little adhesion was observed on the surface of the lens, which was within the allowable level as a projection system for fabricating devices. Also, the surfaces of lenses lying on both sides of the lens had significantly little adhesion. This shows that the TiO_2 film is effective at improving the surrounding atmosphere.

FIG. 2 is a schematic diagram of a portion of a plurality of lenses constituting a projection optical system 4 for a stepper. In this drawing, symbol L1 represents a lens that is applied with a TiO_2 film t. Symbols L2 and L3 represent lenses that are not treated with TiO_2 .

Example 2

A TiO_2 film at a thickness of 20 nm was evaporated by a sputtering system onto the surface of the peripheral area of a portion of lenses constituting a projection optical system composed of fluorite for a KrF stepper (a step-and-repeat or step-and-scan reduction-type projection aligner). The portion of lenses corresponded to one lens out of the total approximately 20 lenses.

In a conventional apparatus, which does not use a TiO_2 film, adhesion was observed on the surface of each lens

constituting a projection optical system after being used for approximately 6 months. In accordance with the present embodiment, only one of the lenses constituting the projection optical system was treated with TiO_2 .

5 Even after being used for several months, the surface of the lens had significantly little adhesion, which was within the allowable level as a projection system for fabricating devices. Also, the surfaces of lenses lying on both sides (i.e., in front and rear) of the lens had
10 significantly little adhesion. This shows that the TiO_2 film is effective at improving the surrounding atmosphere.

FIG. 3 is a schematic diagram of a portion of a plurality of lenses constituting a projection optical system
15 4. In this drawing, a TiO_2 film t is provided on the periphery of a central lens L1. Symbols L2 and L3 represent lenses that are not treated with TiO_2 .

Example 3

A TiO_2 film at a thickness of 20 nm was formed by a
20 dipping process onto the surface of a reflecting mirror among the optical units used for an illumination system of a stepper. In more detail, after a solution of alkyltitanate in butanol was applied onto both surfaces of the reflecting mirror by using a growth method, heat treatment was
25 performed at approximately 350°C to form the film by hydrolysis.

As a result of an inspection of the surface of the reflecting mirror after being used for 6 months, significantly less contamination (adhesion) was observed in comparison with the conventional apparatus, and thus the effectiveness of the TiO_2 film was confirmed. Also, the formation of the TiO_2 film onto the periphery of the mirror, off the optical axis, exhibited the same effect. This shows that the TiO_2 film is effective at improving the surrounding atmosphere.

Example 4

A TiO_2 film was formed by performing surface treatment onto the supporting units in the lens barrel supporting the individual units of the optical system in a stepper, a shade plate, a diaphragm, a shutter, and the like by using processes such as a vapor deposition process and a dipping process described in Examples 1 through 3.

As a result of a contamination inspection of the surfaces after 6 months' operation, a significantly small loss of transmittance, resulting from contamination on the surfaces of the lenses and optical elements provided with the TiO_2 film, was observed, in comparison with the conventional case in which no TiO_2 film was used.

FIG. 4 is a schematic diagram showing an example in which a TiO_2 film is provided on a portion of a holding frame LP for holding lenses L1, L2, and L3 among a portion

of lenses constituting a projection optical system 4. The reflected light (ultraviolet light) from a lens surface enters into the TiO_2 film t, and TiO_2 functions as a photo semiconductor by absorbing ultraviolet light.

5 With respect to a unit that does not transmit light as described above, the TiO_2 film absorbs ultraviolet light from scattered light or the like and functions as a photo semiconductor.

Example 5

10 A TiO_2 film was formed onto the surfaces of a prism, a binary optical element, a diffraction grating, a polarizer, a diffuser, fly's eye lenses, and the like, by using processes such as a vapor deposition process and a dipping process in accordance with Examples 1 through 3. When far
15 ultraviolet rays generated from an excimer laser or the like were used, significantly low contamination was observed in comparison with the conventional cases.

Example 6

20 A semiconductor device was fabricated by using ArF excimer and KrF excimer steppers including optical lenses, optical elements, and lens barrels provided with the TiO_2 film formed by processes in accordance with Examples 1
25 through 5. As a result of an inspection after the device had been used in a predetermined wafer process for 6 months, a small loss of transmittance and little contamination,

which were within the allowable levels, were observed.

Example 7

A TiO_2 film at a thickness of 10 nm was evaporated by a resistance heating evaporation system onto the surface of a binary optics lens (BO lens), i.e., a diffraction optical element, among the lenses constituting a projection optical system composed of quartz for a KrF stepper (a step-and-repeat or step-and-scan reduction-type projection aligner). The BO lens was one of approximately 20 lenses constituting the projection optical system.

In a conventional apparatus that does not use a TiO_2 film, adhesion was observed on the surface of each lens constituting a projection optical system after being used for approximately 6 months. In accordance with the present embodiment, only one BO lens among the lenses constituting the projection optical system was treated with TiO_2 .

When the surface of the BO lens was inspected after a steady operation for 6 months, significantly little adhesion was observed on the surface of the BO lens treated with TiO_2 , which was within the allowable level as a projection optical system for fabricating devices. Also, the surfaces of the lenses lying on both sides of the BO lens had significantly little adhesion. This shows that the TiO_2 film is effective at improving the surrounding atmosphere.

FIG. 5 is a schematic diagram of a portion of a

plurality of lenses constituting a projection optical system 4 for a stepper. In this drawing, symbol L1 represents a BO lens that is applied with a TiO_2 film t. Symbols L2 and L3 represent lenses that are not treated with a TiO_2 film.

5 Symbol BO represents a binary surface.

Example 8

10 A TiO_2 film at a thickness of 20 nm was evaporated by a sputtering system onto the surface of a BO lens among units constituting a projection optical system composed of fluorite for an ArF stepper (a reduction-type projection aligner). The BO lens treated with TiO_2 was one out of the total approximately 20 lenses constituting the optical unit.

15 FIG. 6 is a schematic diagram of a diffraction optical element unit provided on the surface of the BO lens. After a TiO_2 film was deposited onto the walls in a slanting direction, the TiO_2 film on the front surface was removed by dry etching from right above to form TiO_2 films only on the walls. In such a case, light loss was smaller, resulting in high performance, in comparison with a case in which a TiO_2 film was provided on the entire surface.

25 In a conventional apparatus, adhesion was observed on the lens surface after being operated for approximately 6 months. On the contrary, significantly little adhesion, which was within the allowable level, was observed on the surface of the BO lens treated with TiO_2 . Also, the surfaces

of the lenses lying on both sides of the BO lens had significantly little adhesion. This shows that the TiO_2 film is effective at improving the surrounding atmosphere.

In the drawing, numeral 11 represents a BO substrate, numeral 12 represents a binary diffraction optical element having 8 steps, and symbol t represents a TiO_2 film.

Example 9

A TiO_2 film at a thickness of 10 nm was formed by a dipping process onto the surface of a BO element among the optical units used for an illumination system of a stepper. In more detail, after a solution of alkyltitanate in butanol was applied onto both surfaces of the BO element by using a growth method, heat treatment was performed at approximately 350°C to form the film by hydrolysis. Further, a TiO_2 film was formed onto the step surface of the BO element by dry-etching from above. A TiO_2 film was formed also on the back surface at the same time.

As a result of an inspection of the surface of the BO element after 6 months' operation, significantly less contamination (adhesion) was observed in comparison with the conventional apparatus, and thus the effectiveness of the TiO_2 film was confirmed.

FIG. 7 is a schematic diagram of the key portion of a BO element in this example. Numeral 21 represents a mirror substrate, numeral 22 represents a binary diffraction

optical element, and symbol t represents a TiO_2 film.

Example 10

A TiO_2 film was provided on a portion of individual units of an optical system of a stepper by using processes such as a vapor deposition process and a dipping process described in Examples 7 through 9, and also a TiO_2 film was formed by performing surface treatment onto the supporting units in the lens barrel supporting the optical units, a shade plate, a diaphragm, and the like.

As a result of a contamination inspection of the surfaces after 6 months' operation, a significantly small loss of transmittance, resulting from contamination on the surfaces of the lenses and optical elements, was observed, in comparison with the conventional case in which no TiO_2 film was used.

Hereinafter, a method for fabricating devices, which uses a system in accordance with the present invention, will be described as an embodiment.

FIG. 8 is a flow chart of the processes for fabricating devices such as chips, for example, ICs and LSIs, liquid crystal panels, or CCDs.

In step 1 (circuit design), a circuit for a device is designed. In step 2 (mask formation), a mask provided with the designed circuit pattern is formed.

On the other hand, in step 3 (wafer fabrication),

wafers are fabricated using silicon or the like.

Step 4 (wafer process) is referred to as a pre-process, in which an actual circuit is formed on the wafer by lithography, using the mask (reticle) 3, the wafer 5, and a projection lens in accordance with the present invention. Step 5 (assembly) is referred to as a post-process, in which the wafer formed in step 4 is processed to form chips, and includes an assembly process (e.g., dicing and bonding), a packaging process (e.g., chip encapsulation), and so on.

In step 6 (inspection), the device fabricated in step 5 is inspected, including, for example, a performance test and an endurance test. In step 7 (shipment), the device is shipped after undergoing the processes described above.

FIG. 9 is a detailed flow chart of the above-mentioned wafer process (step 3).

In step 11 (oxidation), the surface of the wafer is oxidized. In step 12 (CVD), an insulation film is formed on the surface of the wafer.

In step 13 (electrode formation), electrodes are formed on the wafer by evaporation. In step 14 (ion implantation), ions are implanted into the wafer. In step 15 (resist processing), a photosensitive material is applied onto the wafer. In step 16 (exposure), the circuit pattern on the reticle is projected and exposed onto the wafer, using a projection lens in accordance with the present invention.

In step 17 (development), the exposed wafer is developed. In step 18 (etching), an area excluding the developed resist is etched. In step 19 (resist stripping), any unnecessary resist after etching is removed.

5 By repeating the steps described above, multiple circuit patterns are formed on the wafer.

In accordance with the fabrication method of the present embodiment, high-integration devices, which were difficult to fabricate in the past, can be easily fabricated.

10 As described above, by using titanium oxide (TiO_2) films properly, the following advantages can be obtained.

(1) Dust and hazardous substances in the air can be prevented from adhering to, or from being deposited onto, the surfaces of optical elements (i.e., optical units) such as lenses, mirrors, and prisms, supporting units for supporting optical units, and barrels for containing optical units. Thus, optical properties do not decrease even after being used for long periods of time, and satisfactory conditions can be maintained. In particular, such an exposure apparatus is suitable for fabricating semiconductor devices, and a method for fabricating devices using the same can be achieved.

20 (2) A decrease in performance resulting from contamination of optical elements, optical systems, semiconductor fabricating apparatuses such as steppers,

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measuring instruments, and the like, which are applicable to ultraviolet light, in particular to far ultraviolet light, can be prevented. Consequently, apparatuses that require minimum maintenance can be obtained, resulting in improvement in productivity.

While the present invention has been described with reference to what are presently considered to be the preferred embodiments, it is to be understood that the invention is not limited to the disclosed embodiments. On the contrary, the invention is intended to cover various modifications and equivalent arrangements included within the spirit and scope of the appended claims. The scope of the following claims is to be accorded the broadest interpretation so as to encompass all such modifications and equivalent structures and functions.

WHAT IS CLAIMED IS:

1. An illuminator for illuminating a surface to be illuminated with a luminous flux from a light source through an illumination system, wherein a titanium oxide film is provided on the surface of at least one unit constituting said illumination system.

2. An illuminator for illuminating a surface to be illuminated with a luminous flux from a light source through an illumination system, wherein a titanium oxide film is provided in at least one region of at least one optical unit among a plurality of optical units.

3. An illuminator for illuminating a surface to be illuminated with a luminous flux from a light source through an illumination system, wherein a titanium oxide film is provided in at least one region of a supporting unit for supporting an optical unit.

4. An illuminator according to any one of claims 1, 2, and 3, wherein said luminous flux comprises ultraviolet light, and said titanium oxide film prevents a contaminant from adhering to and contaminating a surface of the unit provided with said titanium oxide film by a photoconductive

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function caused by the absorption of said ultraviolet light.

5. An illuminator according to claim 1, wherein said unit comprises at least one of a diaphragm, a shutter, and a lens barrel.

6. An illuminator according to either claim 1 or 2, wherein said unit comprises at least one of a lens, a mirror, a prism, a filter, a diffuser, a diffraction optical element, and an optical integrator.

7. An illuminator according to claim 2, wherein said optical unit comprises a diffraction optical lens using a diffraction optical element.

8. An illuminator according to claim 2, wherein said optical unit comprises a mirror.

9. An illuminator according to claim 2, wherein said titanium oxide film is provided on the surface of a portion of a region of said optical unit in which light passes through.

10. An illuminator according to any one of claims 1 to 9, wherein said titanium oxide film has a thickness ranging

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from 10 nm to 100 nm.

11. An exposure apparatus for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and exposing a wafer with said pattern, wherein a titanium oxide film is provided on the surface of at least one unit.

12. An exposure apparatus for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and exposing a wafer with said pattern, wherein a titanium oxide film is provided on the surface of at least one region of at least one optical unit among a plurality of optical units.

13. An exposure apparatus for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and exposing a wafer with said pattern, wherein a titanium oxide film is provided on the surface of at least one region of a supporting unit for supporting at least one optical unit.

14. An exposure apparatus according to any one of claims 11, 12, and 13, wherein said luminous flux comprises ultraviolet light, and said titanium oxide film prevents a

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contaminant from adhering to and contaminating a surface of the unit provided with said titanium oxide film by a photoconductive function caused by the absorption of said ultraviolet light.

15. An exposure apparatus according to claim 11, wherein said unit comprises at least one of a diaphragm, a shutter, and a lens barrel.

16. An exposure apparatus according to claim 12, wherein said optical unit comprises at least one of a lens, a mirror, a prism, a filter, a diffuser, a diffraction optical element, and an optical integrator.

17. An exposure apparatus according to claim 12, wherein said optical unit comprises a diffraction optical lens using a diffraction optical element.

18. An exposure apparatus according to claim 12, wherein said optical unit comprises a mirror.

19. An exposure apparatus according to claim 12, wherein said titanium oxide film is provided on the surface of a portion of a region of said optical unit in which light passes through.

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20. An exposure apparatus according to any one of claims 11 to 19, wherein exposure is performed while the pattern on said mask and said wafer are synchronously scanned.

21. An exposure apparatus according to any one of claims 11 to 20, wherein said titanium oxide film has a thickness ranging from 10 nm to 100 nm.

22. A method for fabricating a device comprising the steps of:

exposing a wafer with a pattern on a reticle after said reticle is aligned with said wafer using an exposure apparatus according to any one of claims 11 to 21; and developing said wafer.

23. A projection aligner for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and projecting said pattern onto a wafer by a projection optical system, wherein a titanium oxide film is provided on the surface of at least one unit.

24. A projection aligner for illuminating a pattern on a mask with a luminous flux from a light source through an

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illumination system and projecting said pattern onto a wafer by a projection optical system, wherein a titanium oxide film is provided on the surface of at least one region of at least one optical unit among a plurality of optical units.

25. A projection aligner for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and projecting said pattern onto a wafer by a projection optical system, wherein a titanium oxide film is provided on the surface of at least one region of a supporting unit for supporting at least one optical unit.

26. A projection aligner according to any one of claims 23, 24, and 25, wherein said luminous flux comprises ultraviolet light, and said titanium oxide film prevents a contaminant from adhering to and contaminating a surface of the unit provided with said titanium oxide film by a photoconductive function caused by the absorption of said ultraviolet light.

27. A projection aligner according to claim 23, wherein said unit comprises at least one of a diaphragm, a shutter, and a lens barrel.

28. A projection aligner according to claim 24,

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wherein said optical unit comprises at least one of a lens, a mirror, a prism, a filter, a diffuser, a diffraction optical element, and an optical integrator.

29. A projection aligner according to claim 24, wherein said optical unit comprises a diffraction optical lens using a diffraction optical element.

30. A projection aligner according to claim 24, wherein said optical unit comprises a mirror.

31. A projection aligner according to claim 24, wherein said titanium oxide film is provided on the surface of a portion of a region of said optical unit in which light passes through.

32. A projection aligner according to any one of claims 23 to 31, wherein projection and exposure are performed while said mask and said wafer are synchronously scanned at a velocity ratio in response to imaging magnification of said projection optical system.

33. A projection aligner according to any one of claims 23 to 32, wherein said titanium oxide film has a thickness ranging from 10 nm to 100 nm.

34. A method for fabricating a device, said method comprising the steps of:

projecting and exposing a wafer with a pattern on a reticle after said reticle is aligned with said wafer using a projection aligner according to any one of claims 23 to 33; and

developing said wafer.

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ABSTRACT OF THE DISCLOSURE

In a projection aligner for illuminating a pattern on a mask with a luminous flux from a light source through an illumination system and projecting the pattern onto a wafer with a projection optical system, a titanium oxide (TiO_2) film is provided on the surface of at least one unit constituting the projection aligner. Thus, contamination of the projection aligner can be prevented.

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FIG. 1

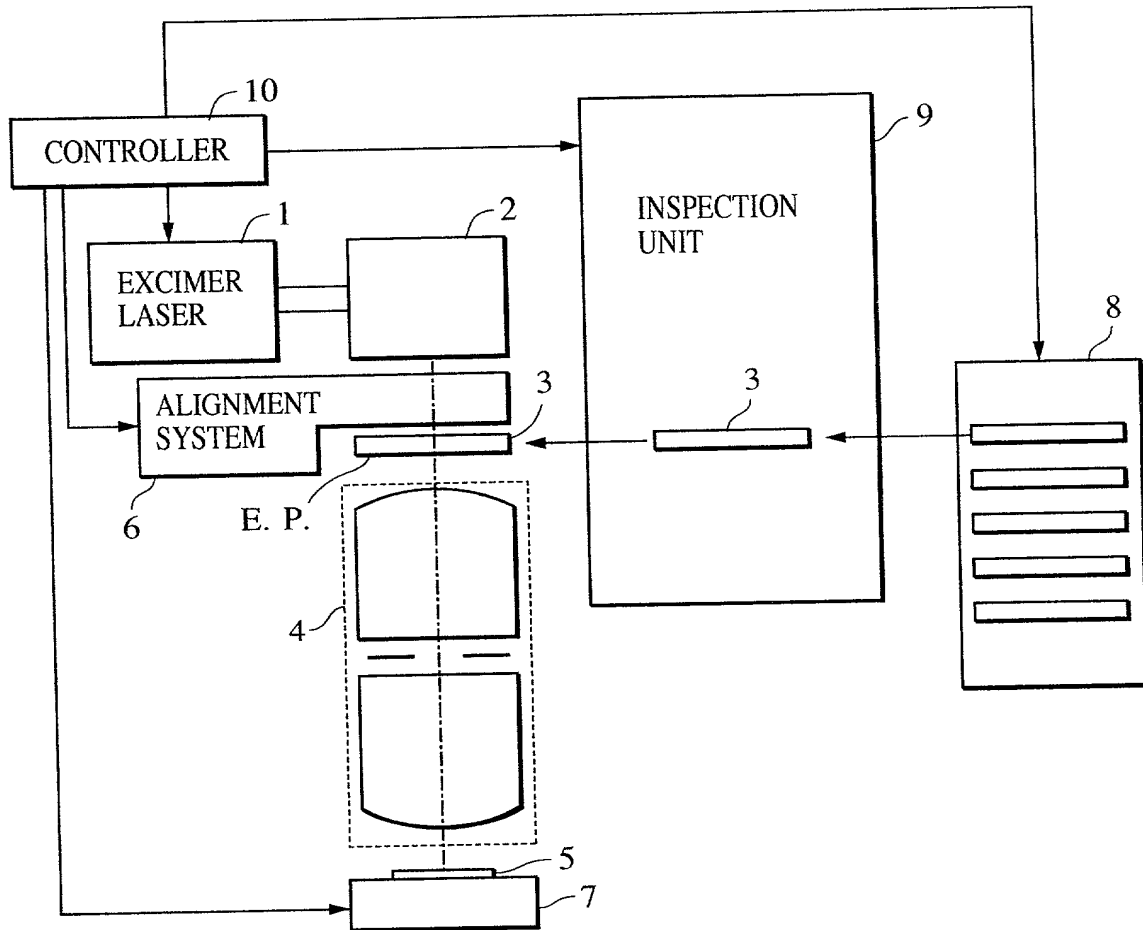


FIG. 2

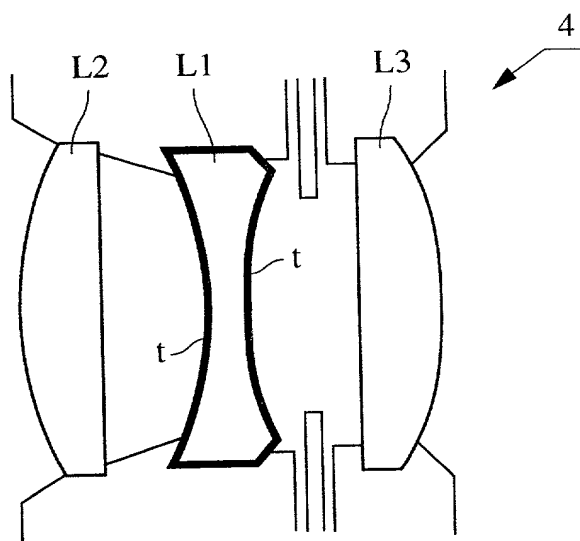


FIG. 3

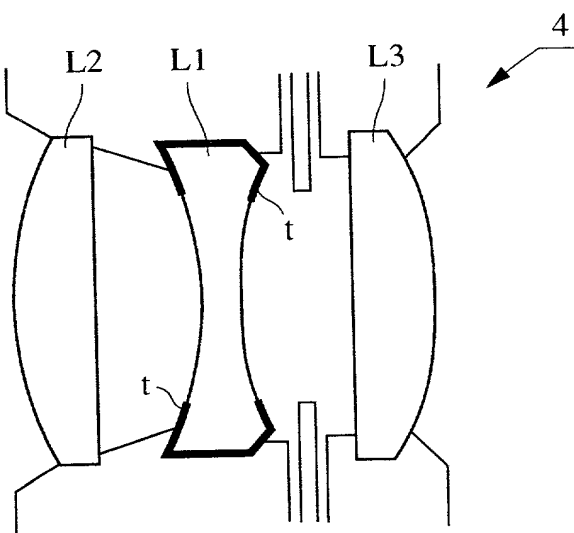


FIG. 4

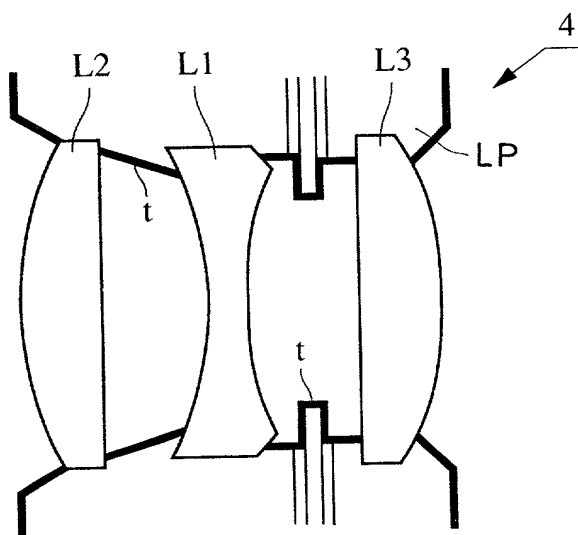


FIG. 5

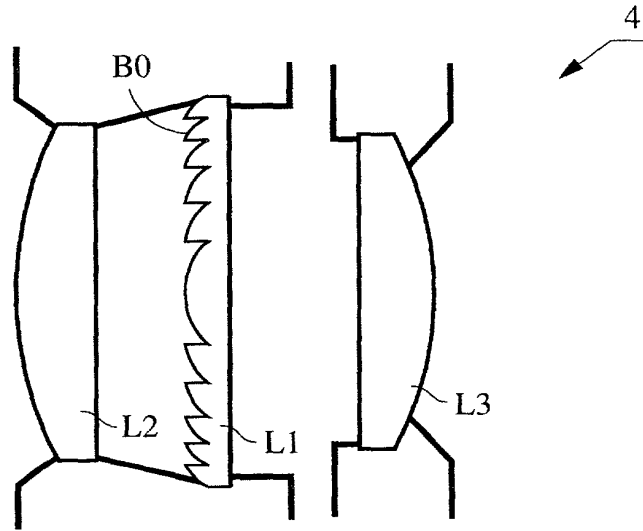


FIG. 6

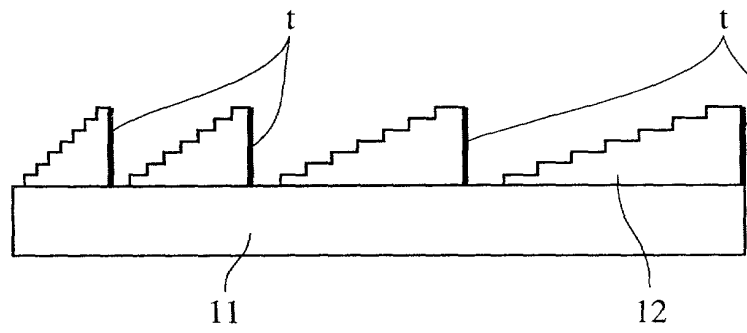


FIG. 7

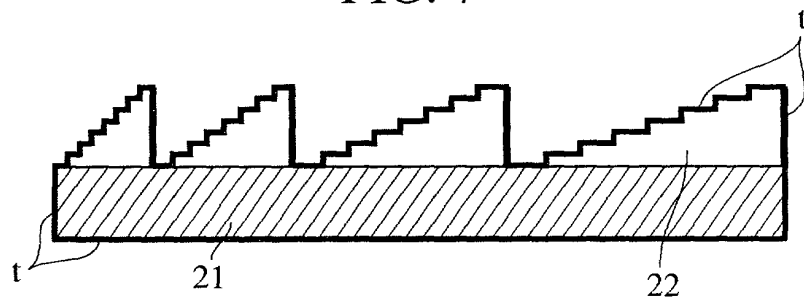


FIG. 8

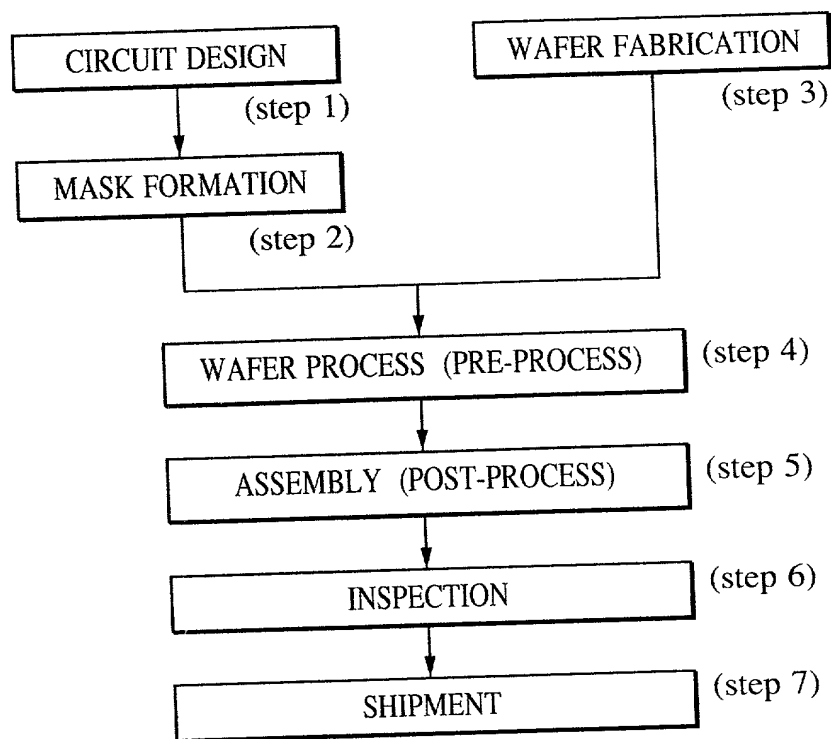
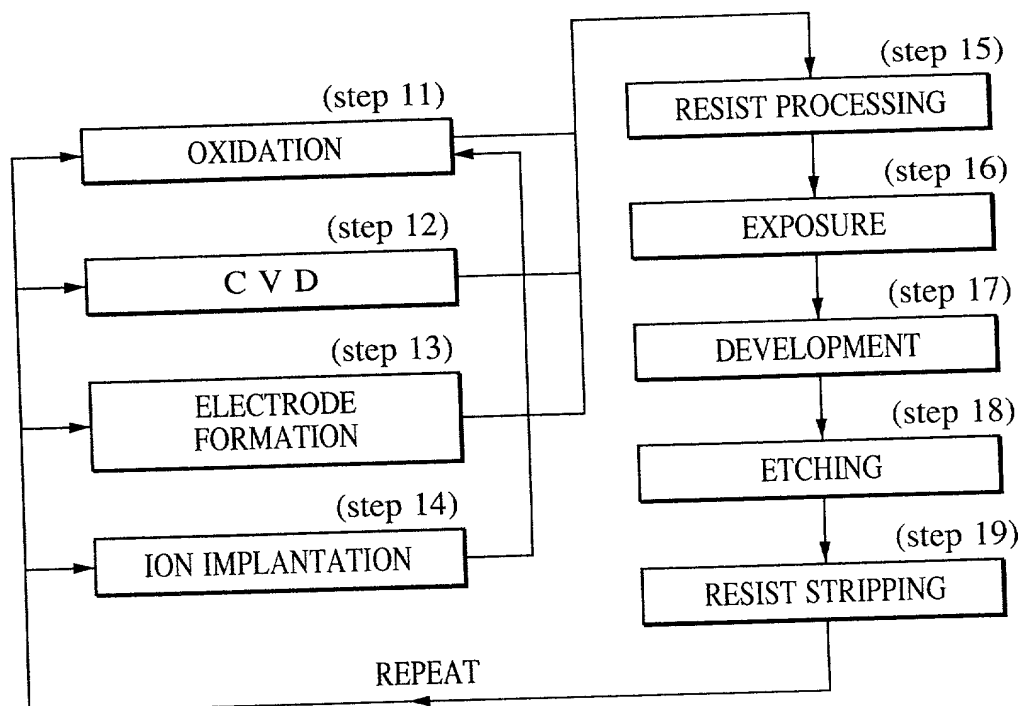


FIG. 9



COMBINED DECLARATION AND POWER OF ATTORNEY
FOR PATENT APPLICATION

(Page 1)

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name;

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled ILLUMINATOR, EXPOSURE APPARATUS, AND METHOD FOR FABRICATING DEVICE USING THE SAME

the specification of which ☒ is attached hereto ☐ was filed on _____ as United States Application No. or PCT International Application No. _____ and was amended on _____ (if applicable).

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in 37 CFR §1.56.

I hereby claim foreign priority benefits under 35 U.S.C. §119(a)-(d) or §365(b), of any foreign application(s) for patent or inventor's certificate, or § 365(a) of any PCT international application which designates at least one country other than the United States, listed below and have also identified below any foreign application for patent or inventor's certificate, or PCT international application having a filing date before that of the application on which priority is claimed:

Country	Application No.	Filed (Day/Mo./Yr.)	(Yes/No) Priority Claimed
JAPAN	09-282995	September 30, 1997	Yes

I hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s), or § 365(c) of any PCT international application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose information which is material to patentability as defined in 37 C.F.R. § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application.

Application No.	Filed (Day/Mo./Yr.)	Status (Patented, Pending, Abandoned)
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I hereby appoint the practitioners associated with the firm and Customer Number provided below to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith, and direct that all correspondence be addressed to the address associated with that Customer Number:

FITZPATRICK, CELLA, HARPER & SCINTO
Customer Number: 05514

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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Inventor's signature _____

Date _____ Citizen/Subject of JAPAN

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COMBINED DECLARATION AND POWER OF ATTORNEY
FOR PATENT APPLICATION
(Page 2)

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ku, Tokyo, Japan

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